

HIGH-FREQUENCY LOW NOISE AMPLIFIER

NPN SILICON EPITAXIAL TRANSISTOR

(WITH BUILT-IN 2 ELEMENTS) MINI MOLD

The μ PA800T has built-in 2 low-voltage transistors which are designed to amplify low noise in the VHF band to the UHF band.

FEATURES

- Low Noise
NF = 1.9 dB TYP. @ f = 2 GHz, $V_{CE} = 1$ V, $I_C = 3$ mA
- High Gain
 $|S_{21e}|^2 = 6.5$ dB TYP. @ f = 2 GHz, $V_{CE} = 1$ V, $I_C = 3$ mA
- A Mini Mold Package Adopted
- Built-in 2 Transistors ($2 \times 2SC4228$)

ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKING STYLE
μ PA800T	Loose products (50 PCS)	Embossed tape 8 mm wide. Pin 6 (Q1 Base), Pin 5 (Q2 Base), Pin 4 (Q2 Emitter) face to perforation side of the tape.
μ PA800T-T1	Taping products (3 KPCS/Reel)	

Remark If you require an evaluation sample, please contact an NEC Sales Representative. (Unit sample quantity is 50 pcs.)

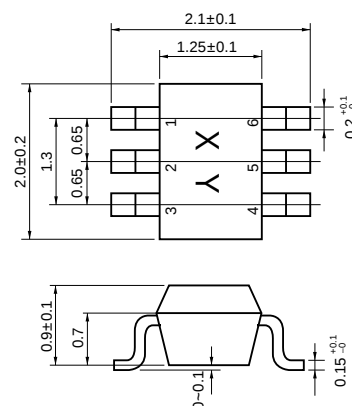
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	10	V
Emitter to Base Voltage	V_{EBO}	1.5	V
Collector Current	I_C	35	mA
Total Power Dissipation	P_T	150 in 1 element 200 in 2 elements ^{Note}	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

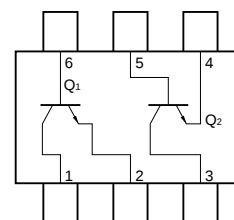
Note 110 mW must not be exceeded in 1 element.

PACKAGE DRAWINGS

(Unit: mm)



PIN CONFIGURATION (Top View)



PIN CONNECTIONS

- | | |
|-------------------|-----------------|
| 1. Collector (Q1) | 4. Emitter (Q2) |
| 2. Emitter (Q1) | 5. Base (Q2) |
| 3. Collector (Q2) | 6. Base (Q1) |

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	I_{CBO}	$V_{CB} = 10\text{ V}, I_E = 0$			1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}$ Note 1	80		200	
Gain Bandwidth Product	f_T	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}$	5.5	80		GHz
Feed-back Capacitance	C_{re}	$V_{CB} = 3\text{ V}, I_E = 0, f = 1\text{ MHz}$ Note 2			0.7	pF
Insertion Power Gain (1)	$ S_{21e} ^2$	$V_{CE} = 1\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$	4.5	6.5		dB
Insertion Power Gain (2)	$ S_{21e} ^2$	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}, f = 2\text{ GHz}$	5.5	7.5		dB
Noise Figure (1)	NF	$V_{CE} = 1\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$		1.9	3.2	dB
Noise Figure (2)	NF	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}, f = 2\text{ GHz}$		1.9	3.2	dB

Notes 1. Pulse Measurement: $P_w \leq 350\text{ }\mu\text{s}$, Duty cycle $\leq 2\%$

2. Measured with 3-pin bridge, emitter and case should be connected to guard pin of bridge.

 h_{FE} CLASSIFICATION

Rank	KB
Marking	RL
h_{FE} Value	80 to 200

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)